

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S3	212	(GaN or (gallium near nitride)) and (single near crystal) and (half near width) and diffraction	US-PGPUB; USPAT	OR	ON	2006/02/04 13:22
S4	87285	nitride and semiconductor and substrate.ab,ti,clm.	US-PGPUB; USPAT	OR	ON	2006/02/03 08:10
S7	129	(gaN or (gallium near nitride)) and semiconductor and substrate and (half near width).ab,ti,clm.	US-PGPUB; USPAT	OR	ON	2006/02/03 08:14
S8	129	(gaN or (gallium near nitride)) and semiconductor and substrate and (half near width).ab,ti,clm.	US-PGPUB; USPAT	OR	ON	2006/02/03 10:17
S9	95	(gaN or (gallium near nitride)) and semiconductor and substrate and (half near width).ab,ti,clm. and density	US-PGPUB; USPAT	OR	ON	2006/02/03 10:18
S10	1341	(428/704).CCLS.	USPAT; USOCR	OR	OFF	2006/02/04 13:24
S12	704	S10 and (Ga or gallium)	US-PGPUB; USPAT	OR	ON	2006/02/04 13:24
S13	208	S10 and (Ga or gallium) and semiconductor	US-PGPUB; USPAT	OR	ON	2006/02/04 13:25
S14	7	S10 and (Ga or gallium) and semiconductor and (half near width)	US-PGPUB; USPAT	OR	ON	2006/02/04 13:25